

**Silicon NPN High Frequency Transistor**

Electrostatic sensitive device.  
Observe precautions for handling.

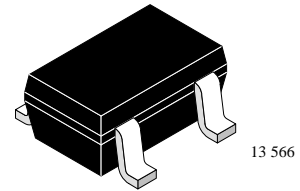
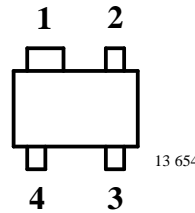
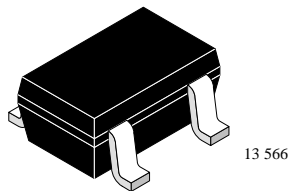
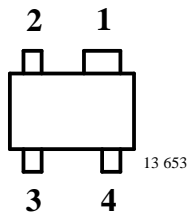


**Applications**

For low-noise and small-signal low-power amplifiers. This transistor has superior noise figure and associated gain performance at UHF, VHF and microwave frequencies.

**Features**

- Low-power applications
- Low noise figure
- High transition frequency



TSDF1205W Marking: WF0  
Plastic case (SOT 343)  
1 = Collector; 2 = Emitter; 3 = Base; 4 = Emitter

TSDF1205RW Marking: W0F  
Plastic case (SOT 343R)  
1 = Collector; 2 = Emitter; 3 = Base; 4 = Emitter

**Absolute Maximum Ratings**

Parameters	Symbol	Value	Unit
Collector-base voltage	$V_{CBO}$	9	V
Collector-emitter voltage	$V_{CEO}$	4	V
Emitter-base voltage	$V_{EBO}$	2	V
Collector current	$I_C$	12	mA
Total power dissipation $T_{amb} \leq 132^\circ\text{C}$	$P_{tot}$	40	mW
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature range	$T_{stg}$	-65 to +150	$^\circ\text{C}$

**Maximum Thermal Resistance**

Parameters	Symbol	Maximum	Unit
Junction ambient, mounted on glass fibre printed board (25 x 20 x 1.5) mm <sup>3</sup> , plated with 35 $\mu\text{m}$ Cu	$R_{thJA}$	450	K/W

## Electrical DC Characteristics

$T_{amb} = 25^{\circ}\text{C}$

Parameters / Test Conditions	Symbol	Min.	Typ.	Max.	Unit
Collector emitter cut-off current $V_{CE} = 12\text{ V}, V_{BE} = 0$	$I_{CES}$			100	$\mu\text{A}$
Collector-base cut-off current $V_{CB} = 10\text{ V}$	$I_{CBO}$			100	nA
Emitter-base cut-off current $V_{EB} = 1\text{ V}$	$I_{EBO}$			2	$\mu\text{A}$
Collector-emitter breakdown voltage $I_C = 1\text{ mA}$	$V_{(BR)CEO}^{1)}$	4			V
Collector-emitter saturation voltage $I_C = 5\text{ mA}, I_B = 0.5\text{ mA}$	$V_{CEsat}$		0.1	0.5	V
DC forward current transfer ratio $V_{CE} = 2\text{ V}, I_C = 2\text{ mA}$	$h_{FE}$	50	120	250	

1)  $t_p / T = 0.01, t_p = 0.3\text{ ms}$

## Electrical AC Characteristics

$T_{amb} = 25^{\circ}\text{C}$

Parameters / Test Conditions	Symbol	Min.	Typ.	Max.	Unit
Transition frequency $V_{CE} = 2\text{ V}, I_C = 5\text{ mA}, f = 1\text{ GHz}$	$f_T$		12		GHz
Collector-base capacitance $V_{CB} = 1\text{ V}, f = 1\text{ MHz}$	$C_{cb}$		0.2		pF
Collector-emitter capacitance $V_{CE} = 1\text{ V}, f = 1\text{ MHz}$	$C_{ce}$		0.35		pF
Emitter-base capacitance $V_{EB} = 0.5\text{ V}, f = 1\text{ MHz}$	$C_{eb}$		0.15		pF
Noise figure $V_{CE} = 2\text{ V}, I_C = 2\text{ mA}, Z_S = Z_{Sopt}, Z_L = 50\ \Omega,$ $f = 2\text{ GHz}$	F		1.3		dB
Power gain $V_{CE} = 2\text{ V}, I_C = 2\text{ mA}, f = 2\text{ GHz}, (@F_{opt})$ $V_{CE} = 2\text{ V}, I_C = 5\text{ mA}, Z_S = Z_{Sopt}, Z_L = 50\ \Omega$ $f = 2\text{ GHz}$	$G_{pe}$ $G_{pe}$		11.5 18		dB dB
Transducer gain $V_{CE} = 2\text{ V}, I_C = 5\text{ mA}, Z_0 = 50\ \Omega, f = 2\text{ GHz}$	$ S_{21e} ^2$		12.5		dB

**Typical Characteristics** ( $T_j = 25^\circ\text{C}$  unless otherwise specified)

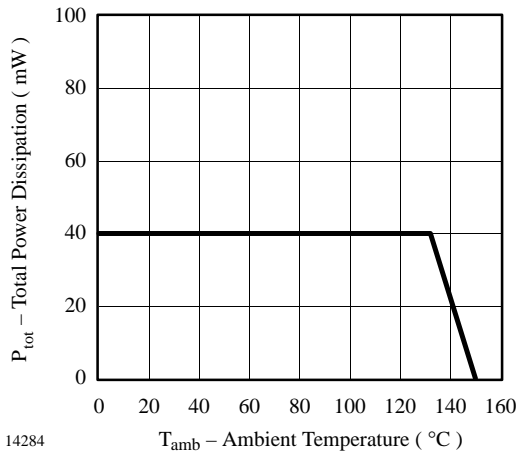


Figure 1.. Total Power Dissipation vs. Ambient Temperature

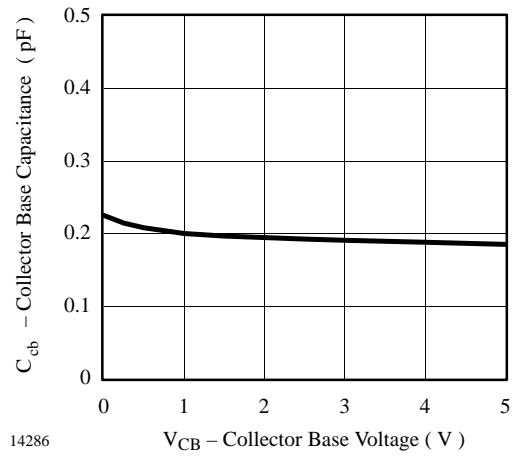


Figure 3.. Collector Base Capacitance vs. Collector Base Voltage

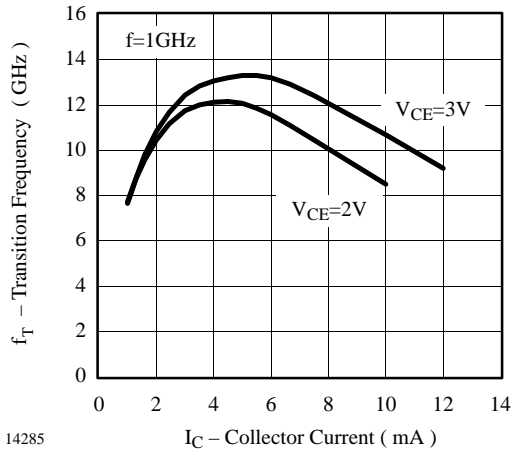


Figure 2.. Transition Frequency vs. Collector Current

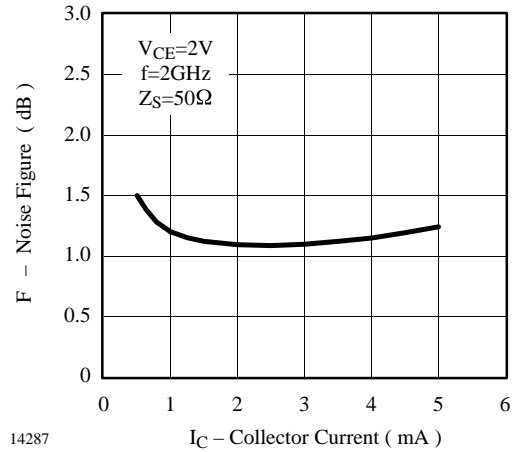
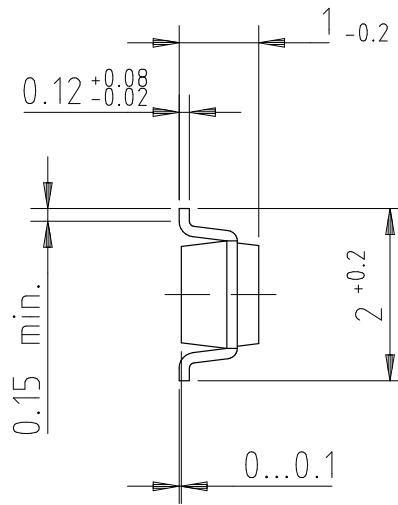
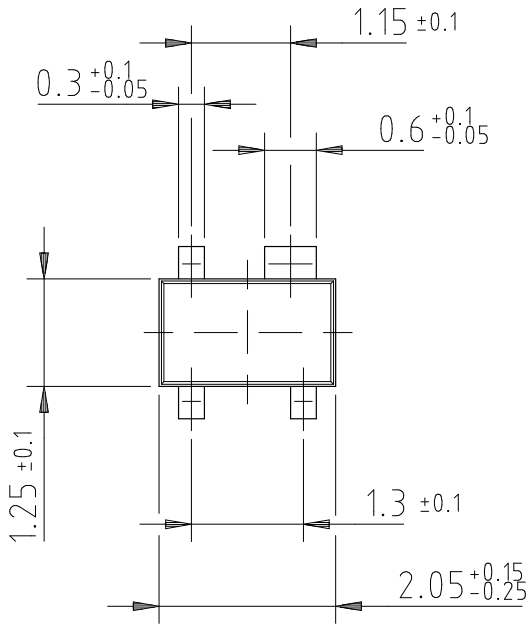
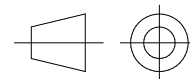


Figure 4.. Noise Figure vs. Collector Current

## Dimensions of TSDF1205W in mm

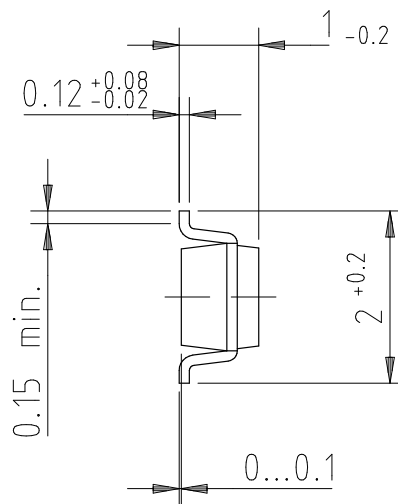
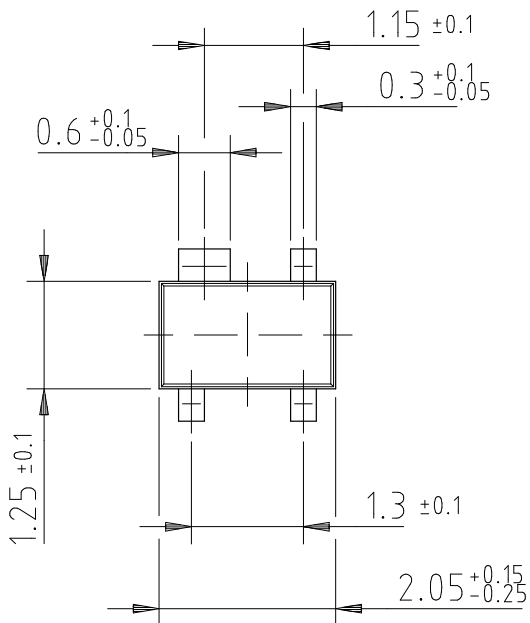


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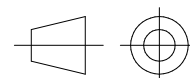


technical drawings  
according to DIN  
specifications

## Dimensions of TSDF1205RW in mm



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technical drawings  
according to DIN  
specifications

## **Ozone Depleting Substances Policy Statement**

It is the policy of **TEMIC TELEFUNKEN microelectronic GmbH** to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

**TEMIC TELEFUNKEN microelectronic GmbH** semiconductor division has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

**TEMIC** can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

**We reserve the right to make changes to improve technical design and may do so without further notice.**

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use TEMIC products for any unintended or unauthorized application, the buyer shall indemnify TEMIC against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

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